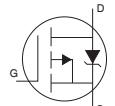


Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.009	—	V/°C	Reference to 25°C , $I_D = -1mA$ ②
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.050	0.065	Ω	$V_{GS} = -4.5V, I_D = -3.7A$ ②
		—	0.080	0.135		$V_{GS} = -2.5V, I_D = -3.1A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.40	-0.55	-1.2	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	6.0	—	—	S	$V_{DS} = -10V, I_D = -3.7A$ ②
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -20V, V_{GS} = 0V, T_J = 70^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -12V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 12V$
Q_g	Total Gate Charge	—	8.0	12	nC	$I_D = -3.7A$
Q_{gs}	Gate-to-Source Charge	—	1.2	1.8		$V_{DS} = -10V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	2.8	4.2		$V_{GS} = -5.0V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	350	—	ns	$V_{DD} = -10V$
t_r	Rise Time	—	48	—		$I_D = -3.7A$
$t_{d(off)}$	Turn-Off Delay Time	—	588	—		$R_G = 89\Omega$
t_f	Fall Time	—	381	—		$R_D = 2.7\Omega$
C_{iss}	Input Capacitance	—	633	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	145	—		$V_{DS} = -10V$
C_{rss}	Reverse Transfer Capacitance	—	110	—		$f = 1.0MHz$

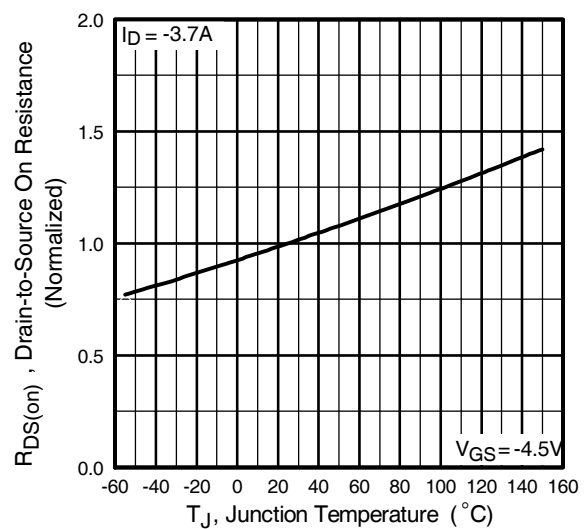
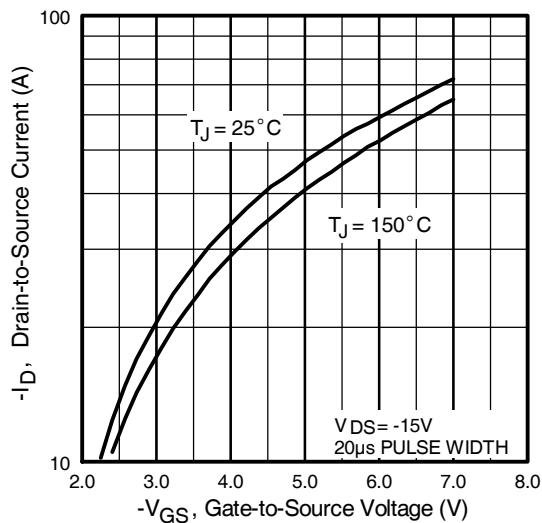
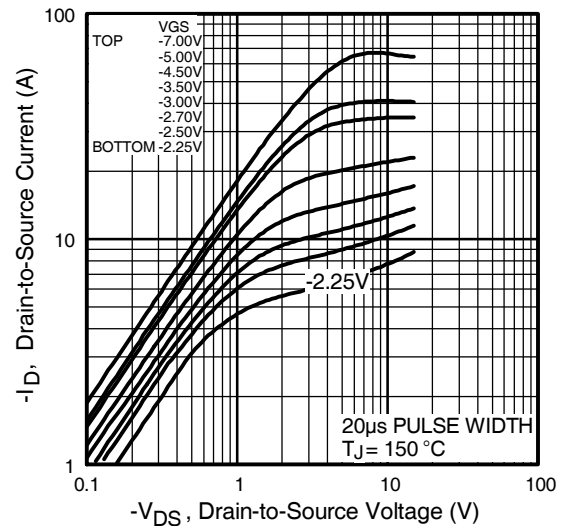
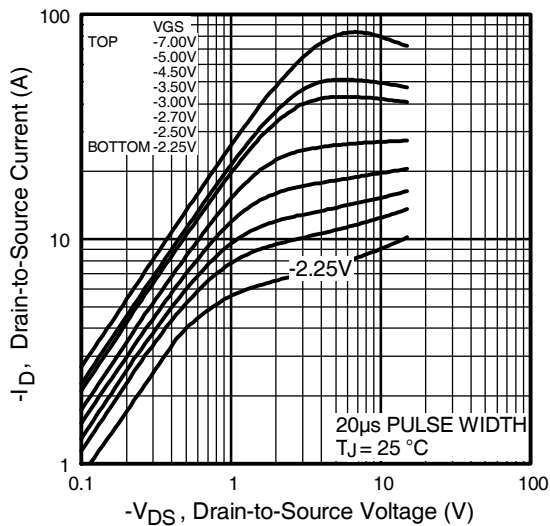
Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-22		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -1.0A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	29	43	ns	$T_J = 25^\circ\text{C}, I_F = -1.0A$
Q_{rr}	Reverse Recovery Charge	—	11	17	nC	$di/dt = -100A/\mu s$ ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ③ Surface mounted on 1" square single layer 1oz. copper FR4 board, steady state.
- ④ Starting $T_J = 25^\circ\text{C}$, $L = 1.65mH$
 $R_G = 25\Omega$, $I_{AS} = -3.7A$.

** For recommended footprint and soldering techniques refer to application note #AN-994.



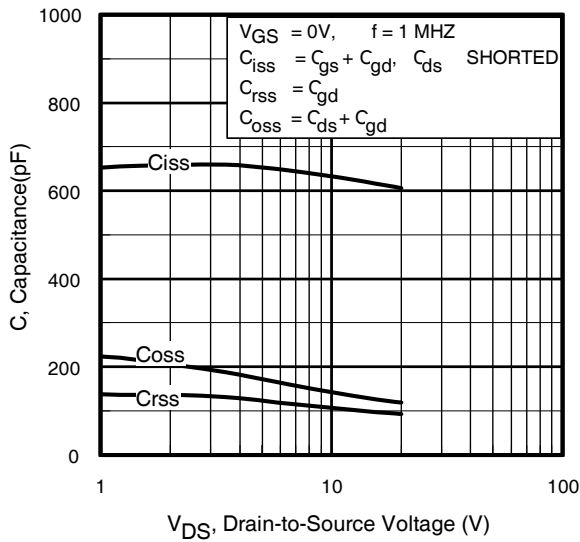


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

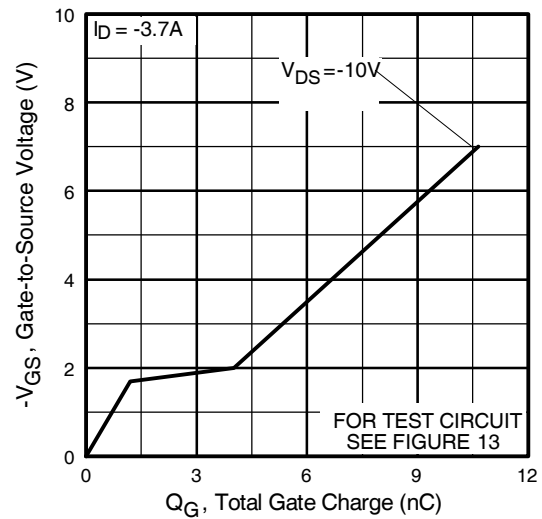


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

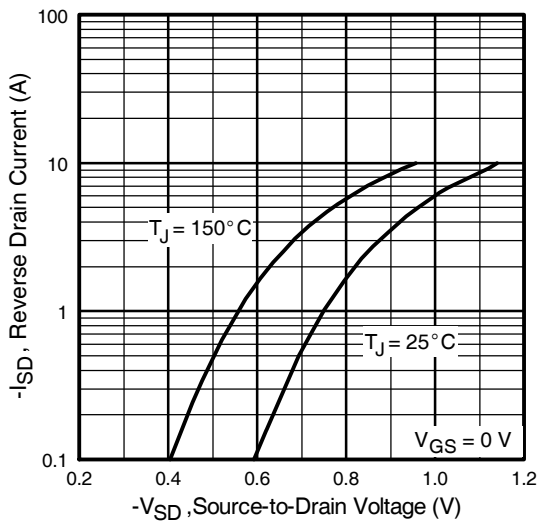


Fig 7. Typical Source-Drain Diode Forward Voltage

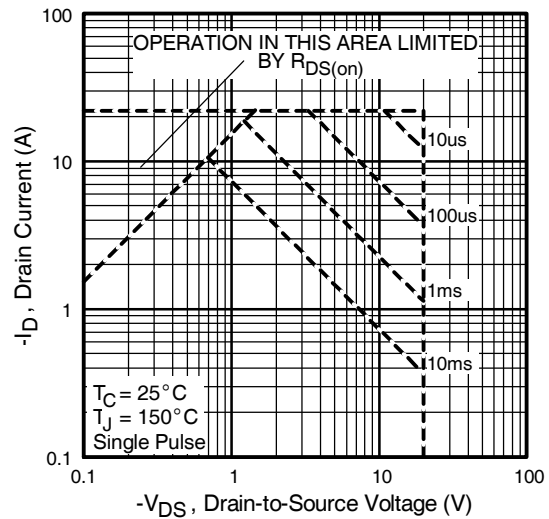


Fig 8. Maximum Safe Operating Area

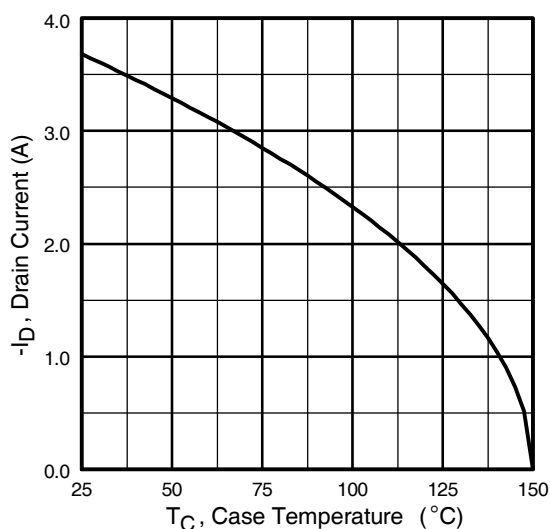


Fig 9. Maximum Drain Current Vs. Case Temperature

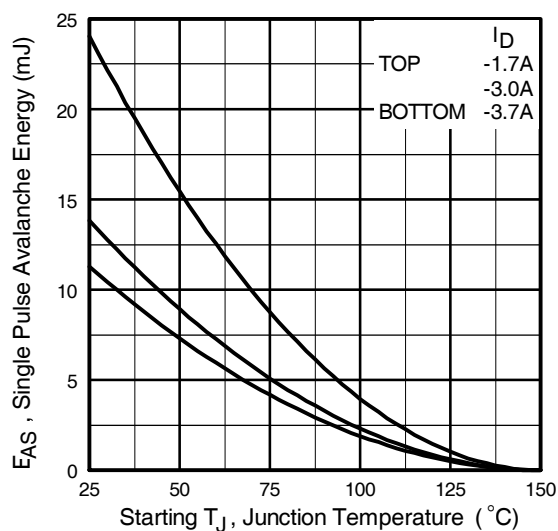


Fig 10. Maximum Avalanche Energy Vs. Drain Current

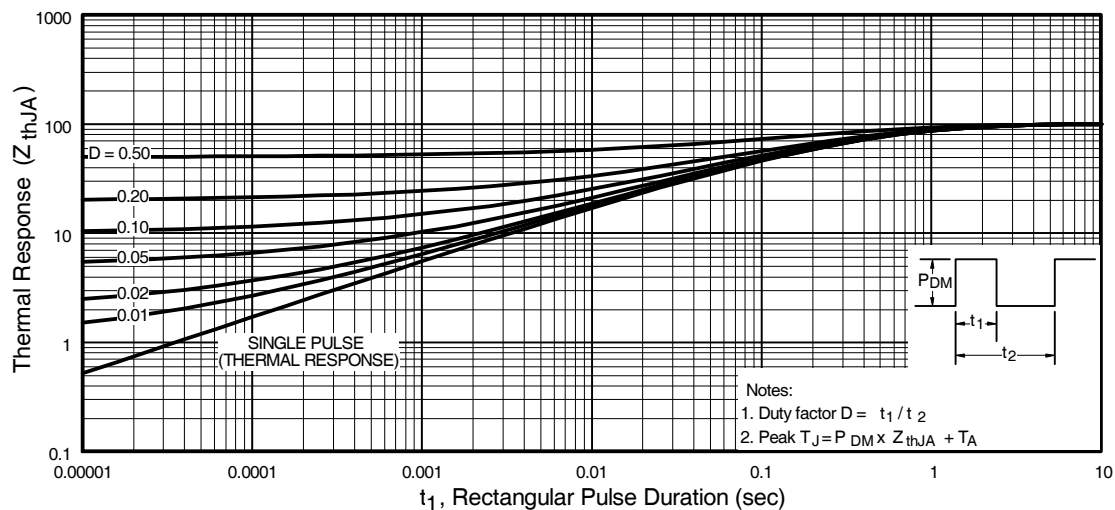


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

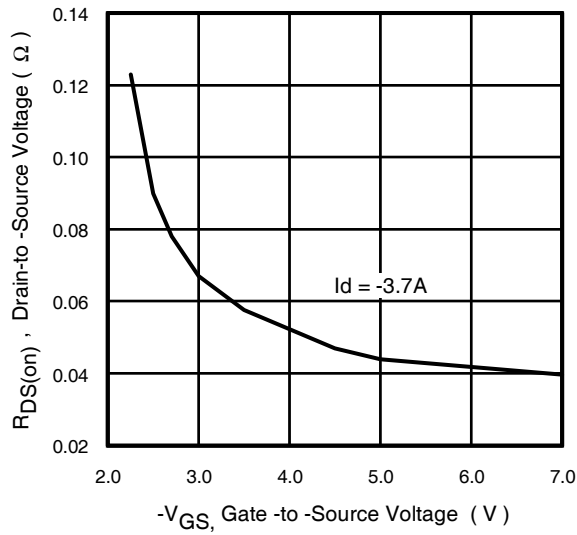


Fig 12. Typical On-Resistance Vs. Gate Voltage

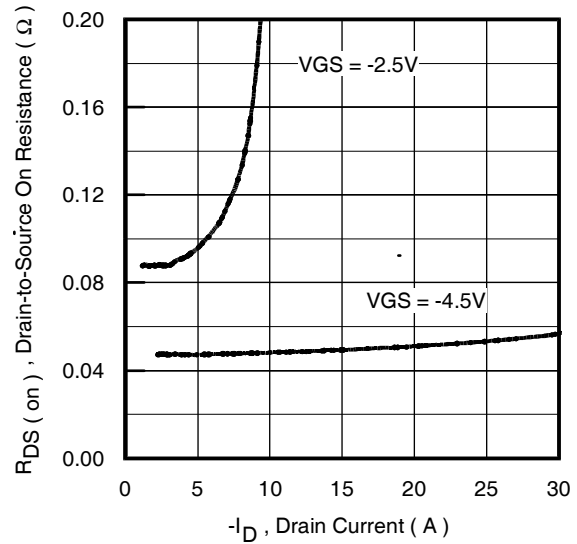


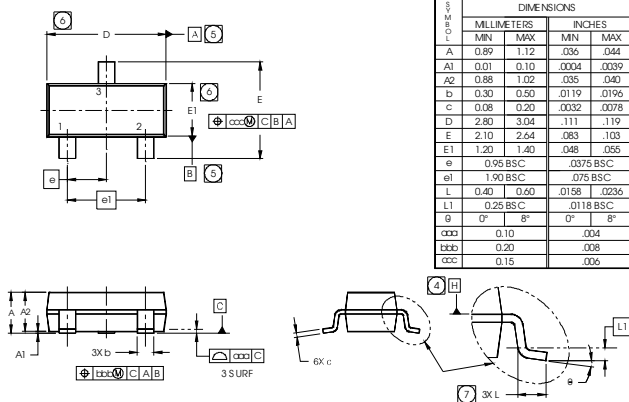
Fig 13. Typical On-Resistance Vs. Drain Current



IRLML6402PbF

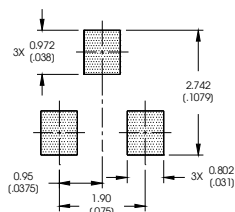
Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	.035	.044
A1	0.01	0.10	.0004	.0039
A2	0.88	1.02	.035	.040
b	0.30	0.50	.0119	.0196
C	0.08	0.20	.0032	.0078
D	2.80	3.04	.111	.119
E	2.10	2.64	.083	.103
E1	1.20	1.40	.048	.055
e	0.95 BSC		.0375 BSC	
el	1.90 BSC		.075 BSC	
L	0.40	0.60	.0158	.0236
L1	0.25 BSC		.0118 BSC	
Q	0°	8°	0°	8°
Q1	0.10		.004	
Q2	0.20		.008	
Q3	0.15		.006	

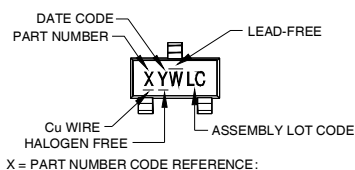
RECOMMENDED FOOT PRINT



- NOTES
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS AND INCHES.
 3. CONTROLLING DIMENSION: MILLIMETER.
 4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
 5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
 6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.
 7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236AB.

Micro3 (SOT-23 / TO-236AB) Part Marking Information

Notes: This part marking information applies to devices produced after 02/26/2001



X = PART NUMBER CODE REFERENCE:

A = IRLML2402	S = IRLML6244
B = IRLML2803	T = IRLML6246
C = IRLML6302	U = IRLML6344
D = IRLML5103	V = IRLML6346
E = IRLML6402	W = IRFML8244
F = IRLML6401	X = IRLML2244
G = IRLML2502	Y = IRLML2246
H = IRLML5203	Z = IRFML9244
I = IRLML0030	
J = IRLML2030	
K = IRLML0100	
L = IRLML0060	
M = IRLML0040	
N = IRLML2060	
P = IRLML9301	
R = IRLML9303	

DATE CODE EXAMPLE:
YWW = 432 = DF
YWW = 503 = 5C

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR		Y	WORK WEEK	W
2011	2001	1	01	A
2012	2002	2	02	B
2013	2003	3	03	C
2014	2004	4	04	D
2015	2005	5		
2016	2006	6		
2017	2007	7		
2018	2008	8		
2019	2009	9		
2020	2010	0	24	X
			25	Y
			26	Z

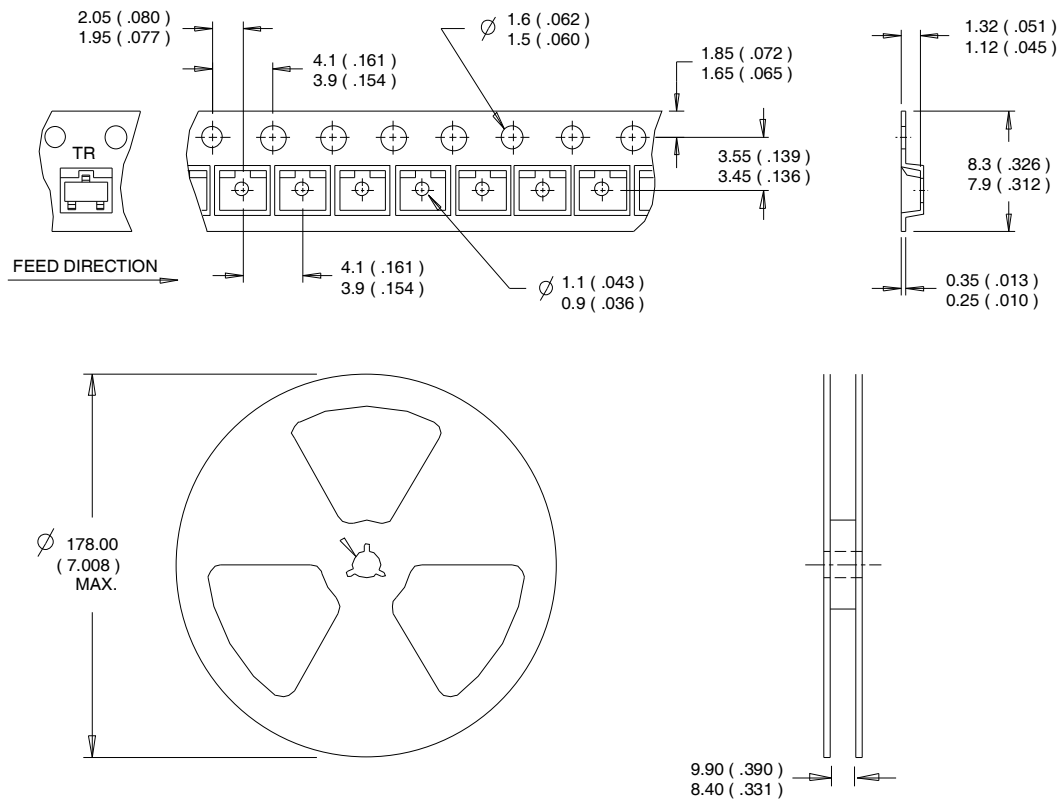
W = (27-52) IF PRECEDED BY A LETTER

YEAR		Y	WORK WEEK	W
2011	2001	A	27	A
2012	2002	B	28	B
2013	2003	C	29	C
2014	2004	D	30	D
2015	2005	E	↓	↓
2016	2006	F		
2017	2007	G		
2018	2008	H		
2019	2009	J		
2020	2010	K	50	X
			51	Y
			52	Z

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

Micro3™(SOT-23/TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

Qualification information[†]

Qualification level	Consumer (per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	Micro3™ (SOT-23)	MSL1 (per JEDEC J-STD-020D ^{††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release

Revision History

Date	Comment
4/28/2014	• Updated data sheet with new IR corporate template. • Updated package outline & part marking on page 7. • Added Qualification table -Qual level "Consumer" on page 9. • Added bullet point in the Benefits "RoHS Compliant, Halogen -Free" on page 1.

International
 Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA
 To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>

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